



Nanoscale heterogeneities at Transition Metal Dichalcogenide-Au Interfaces

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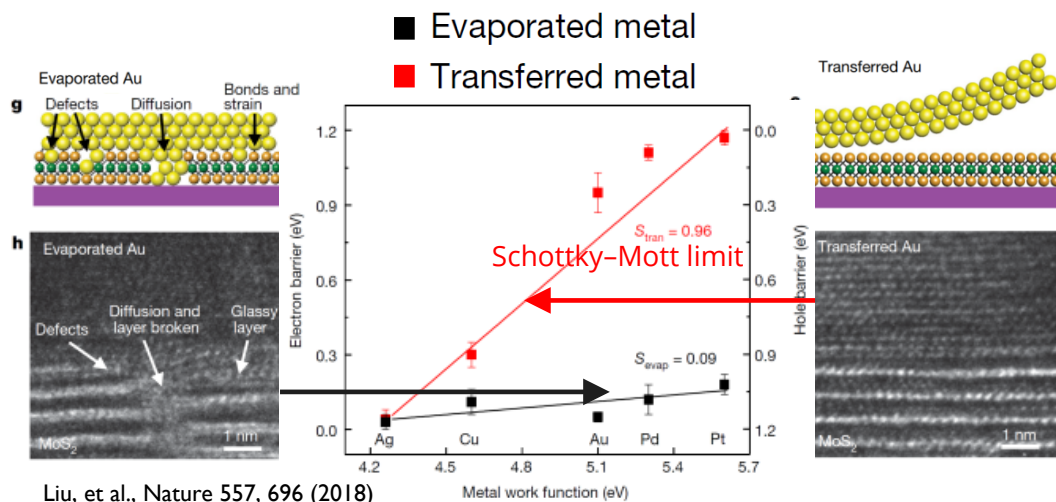
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TMD-metal contact impacts device performance

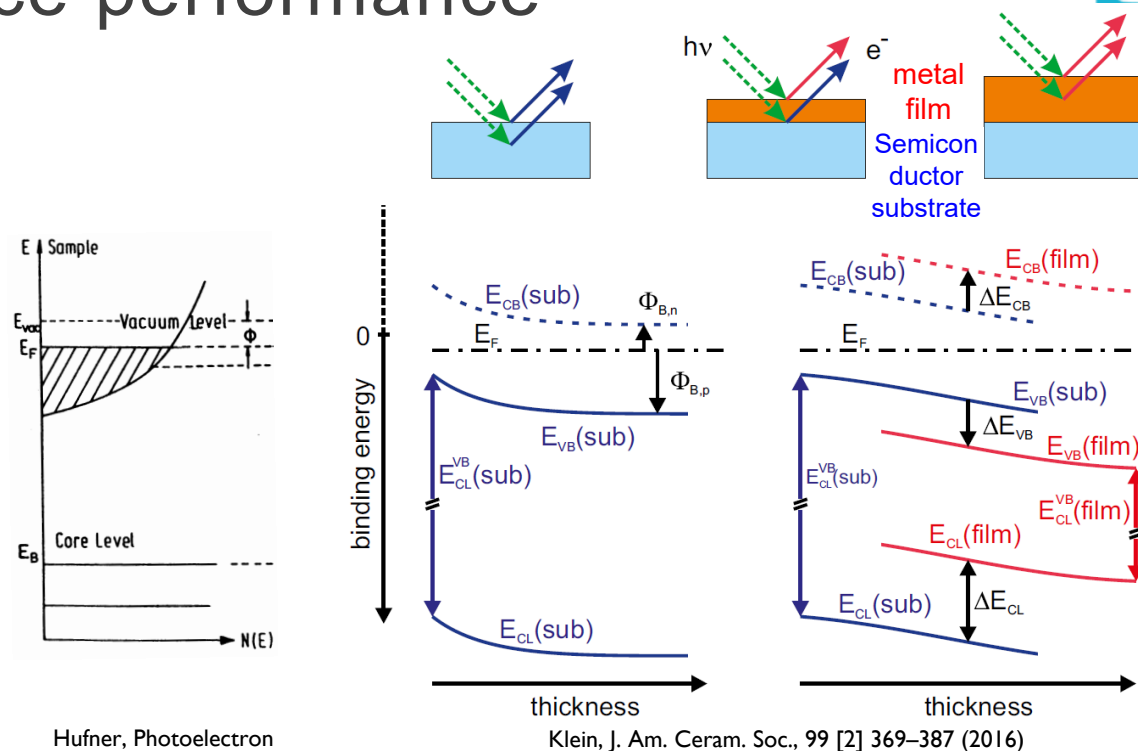
- **Transition metal dichalcogenides (TMD)** is a new class of **semiconductors** with enormous technological implications
- **TMD-metal contact is a critical component** to incorporate 2D materials in electronic devices

Questions:

- What are the difference of the TMD-metal interfaces fabricated via evaporation vs transfer?
- Are there heterogeneities in the electronic structure at the TMD-metal interfaces?
 - Impacts of the microstructures of Au or TMD?



Liu, et al., Nature 557, 696 (2018)

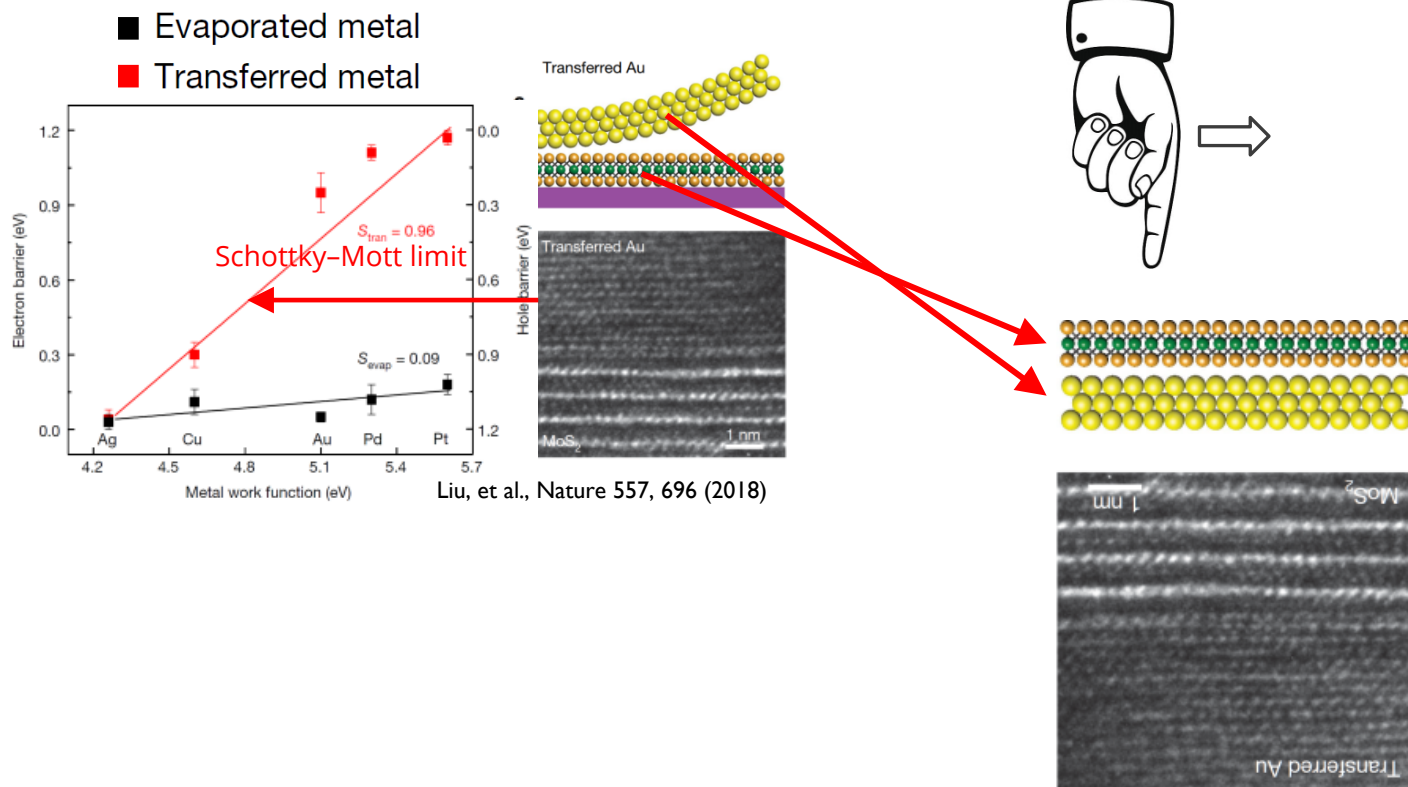


Challenges in examining TMD-metal contact using photoelectron spectroscopy:

- Object of interest is buried preventing direct access to the valence states
 - Energetics of valence states are inferred from the core level assuming $E_{\text{CL}}^{\text{VB}}(\text{sub})$ and $E_{\text{CL}}^{\text{VB}}(\text{film})$ stay unchanged
 - $E_{\text{CL}}^{\text{VB}}(\text{sub})$, $E_{\text{CL}}^{\text{VB}}(\text{film})$, & bandgap may not be constant since TMDs are susceptible to screening environment

- **How about upside-down geometry?**

Upside-down geometry enables access to the electronic structure of the TMD & interfaces

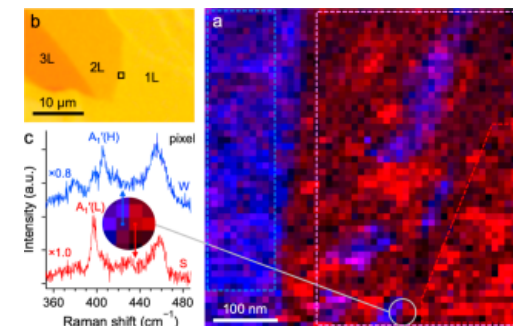
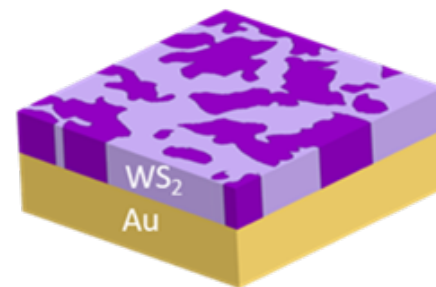


Upside-down geometry enables access to:

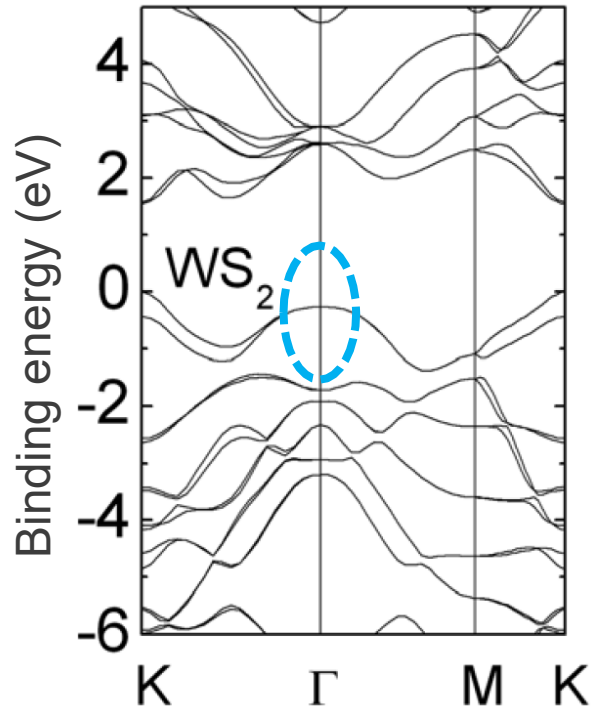
- valence band density of states in TMD
- electronic structure of a metal film (when TMD is thin)
- atomic arrangement & microstructures of TMD & metal grains

System 1: WS₂ exfoliated on a freshly deposited polycrystalline Au film

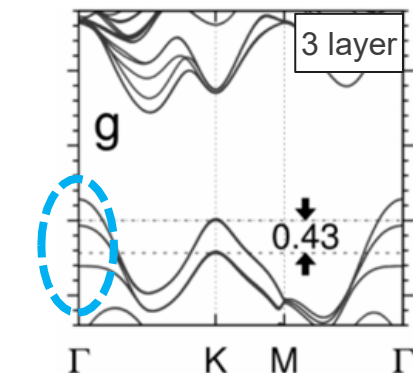
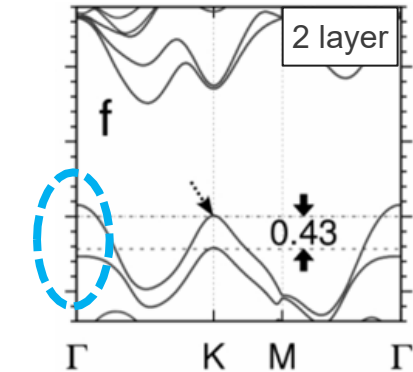
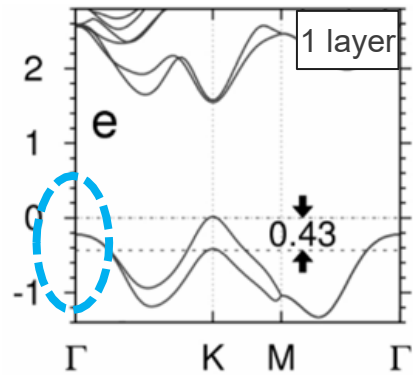
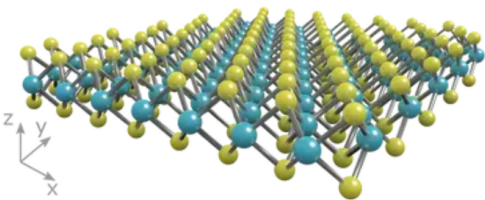
- A similar system (MoS₂ on Au) shows local variations of the surface potential, conductance, & Raman response
- Direct probe the electronic structures is desirable



Photoelectron spectra reflect the electron dispersion of the sample



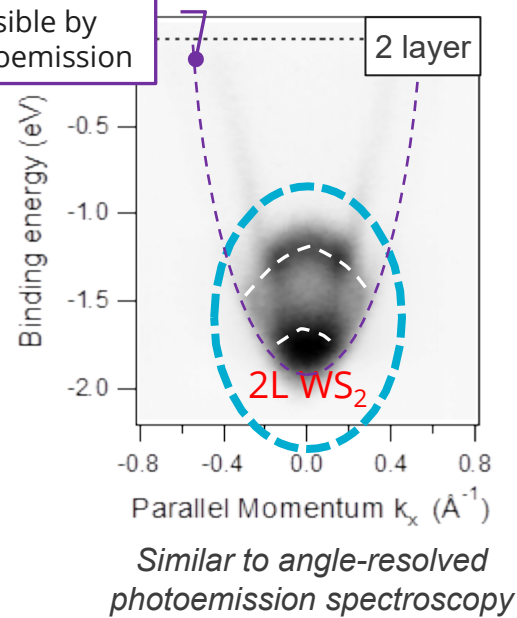
Kang, et al., APL 102, 012111 (2013)



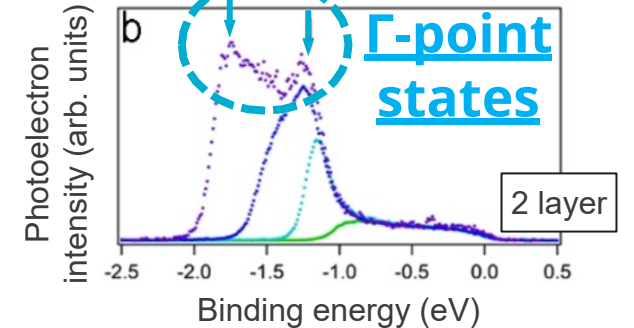
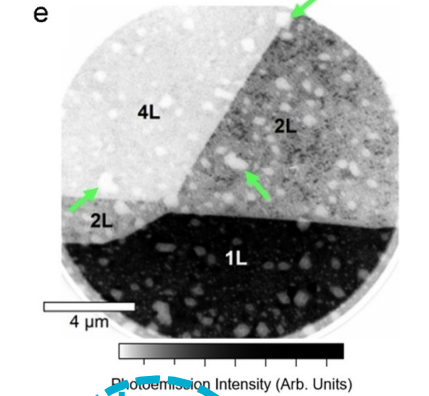
Zeng, et al., Scientific Reports 3, 1608 (2013)

Reciprocal space PEEM

Accessible by
UV-photoemission



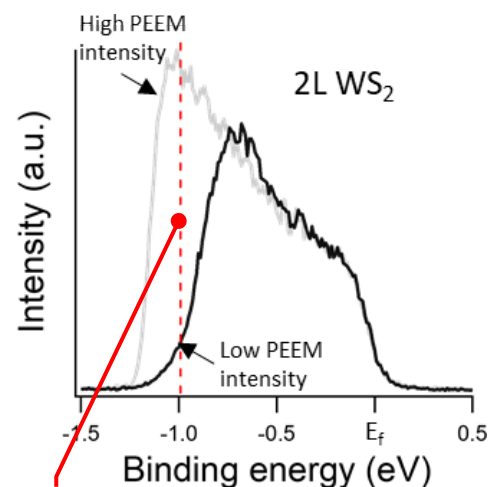
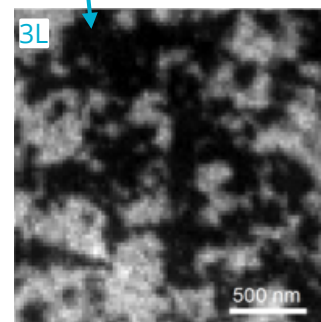
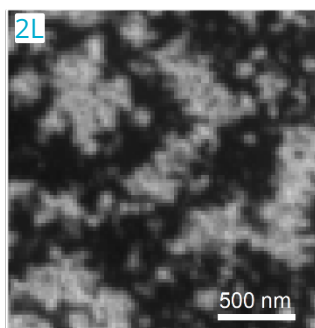
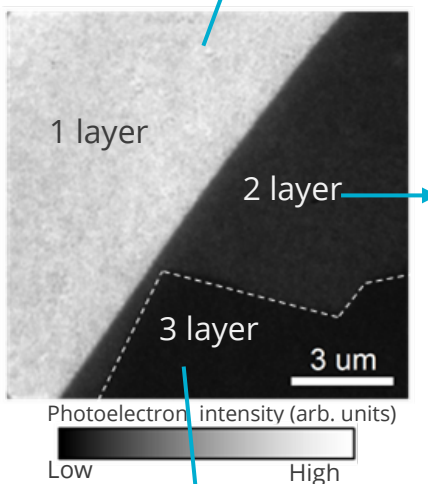
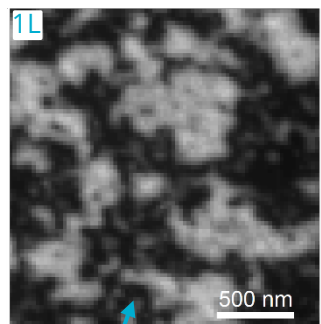
Real space PEEM



- PEEM probes the occupied electronic states in real space & reciprocal space

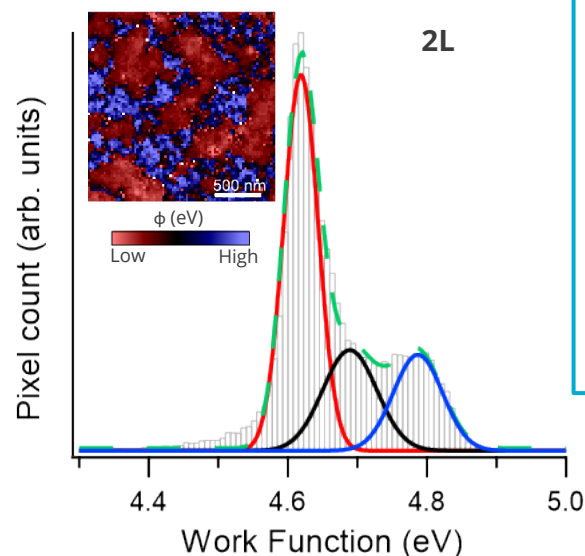
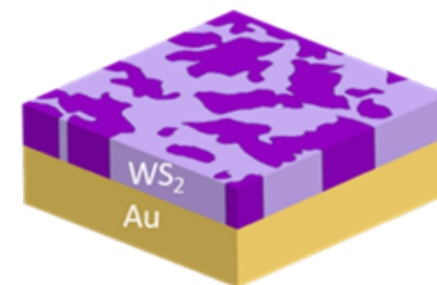
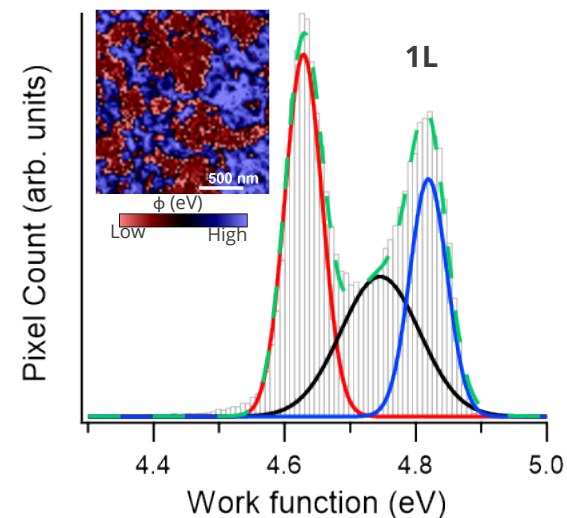
- Deep UV-photoemission probes the states only near the Brillion zone center (i.e., Γ -point)

We observe submicron-scale work function heterogeneity in WS₂ exfoliated on freshly-deposited Au



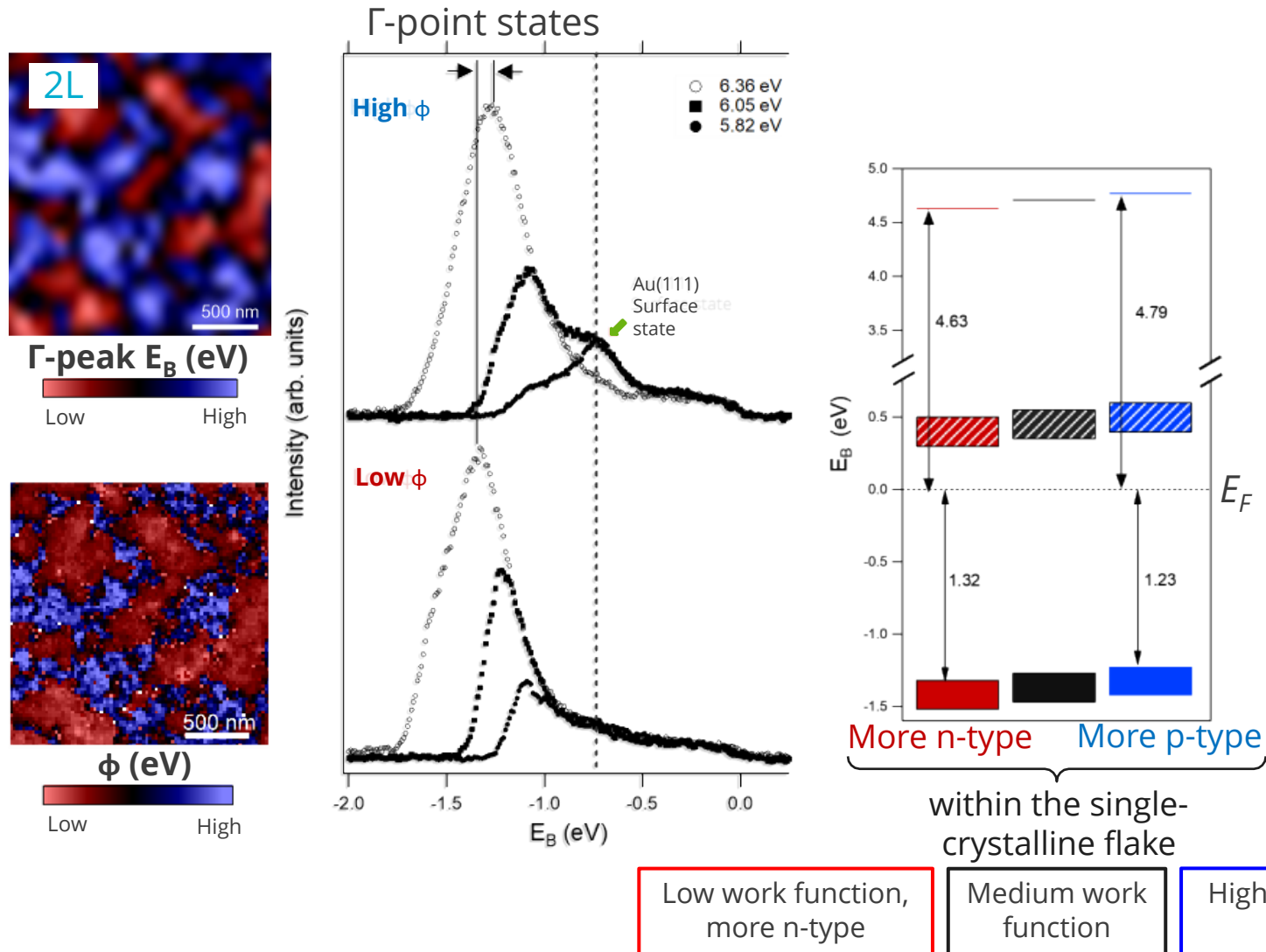
PEEM contrasts arise from difference in work function

- Contrasting μm sized domains in PEEM intensity
- Present in 1-3L WS₂ thickness



- Large work function variation (>200 meV)
- Varying carrier density within the WS₂ flake

We determine submicron-scale carrier density variations in freshly-deposited Au-WS₂ interfaces

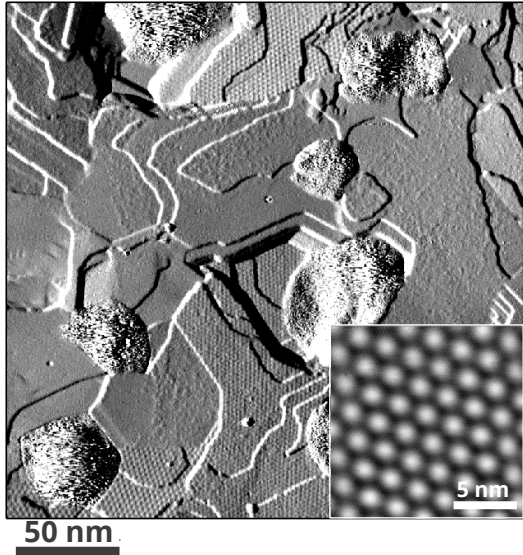


- Same micron-sized domains from photoelectron intensity & work function (ϕ) maps
- Higher work function regions show corresponding upshift in VBM
- Low BE peak (-0.7eV) observed near fermi level only in high work function areas
 - **Au (111) surface state:** impact of substrate?
- **Schottky barrier height appears to vary by ~0.1eV across the metal contact**

Three predominant crystallographic orientations of the Au grains elucidated via EBSD



WS₂ covered as-deposited Au

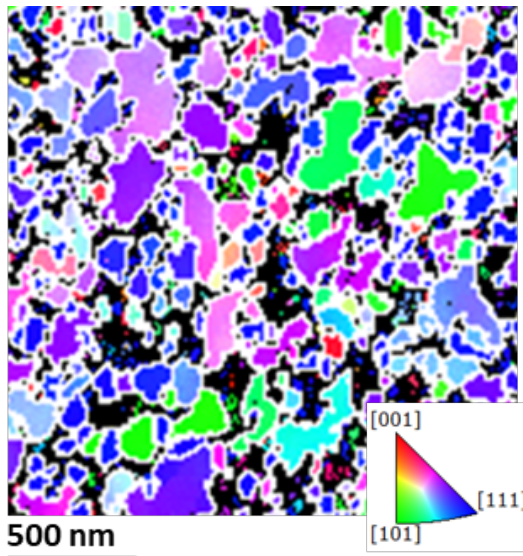


Scanning tunneling microscopy:

- Atomic terraces of Au & trapped blisters
- Hexagonal Moiré patterns indicate closely adhered WS₂ to Au & van der Waals interface

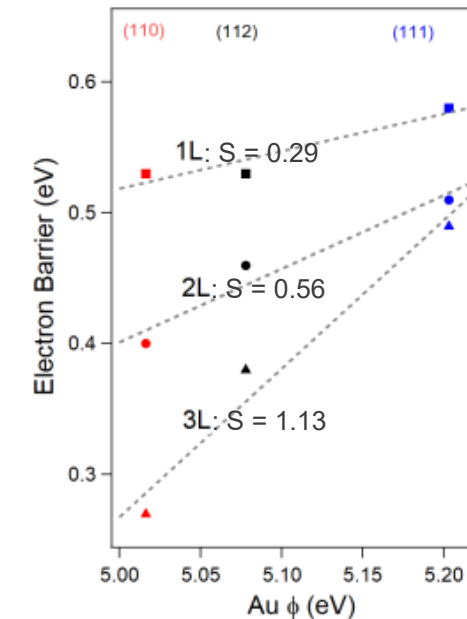
EBSD: Electron Backscatter Diffraction

- Majority of Au grains have (111), (112), or (110) facets according to inverse pole figure
- Consistent with localization of Moiré patterns in STM and Au(111) surface state in PEEM
- Same length scale as heterogenous electronic structure domains



Au	(110)	(112)	(111)	$\Delta\phi_{\text{Au}}$ (eV)
ϕ_{Au} (eV)	5.02	5.08	5.2	0.18
WS ₂	1L	2L	3L	
$\Delta\phi_{\text{WS}_2}$ (eV)	0.18	0.16	0.13	

$\Delta\phi_{\text{Au}} \approx \Delta\phi_{\text{WS}_2}$



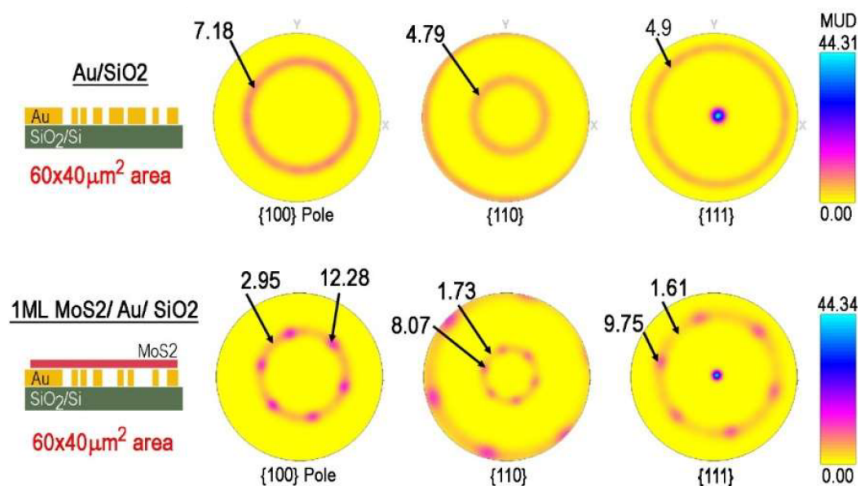
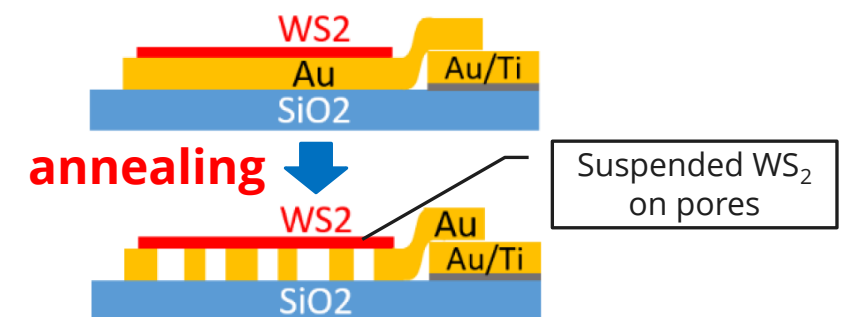
Take-home messages:

- **3 different Schottky barriers** within a single junction
- **Crystal facets of Au grains** govern the **Schottky barrier height** between Au & WS₂
- Relatively high S (pinning factor or interface parameter) expected for van der Waals bonding

What happens if there are WS_2 -Au(111) interfaces only?

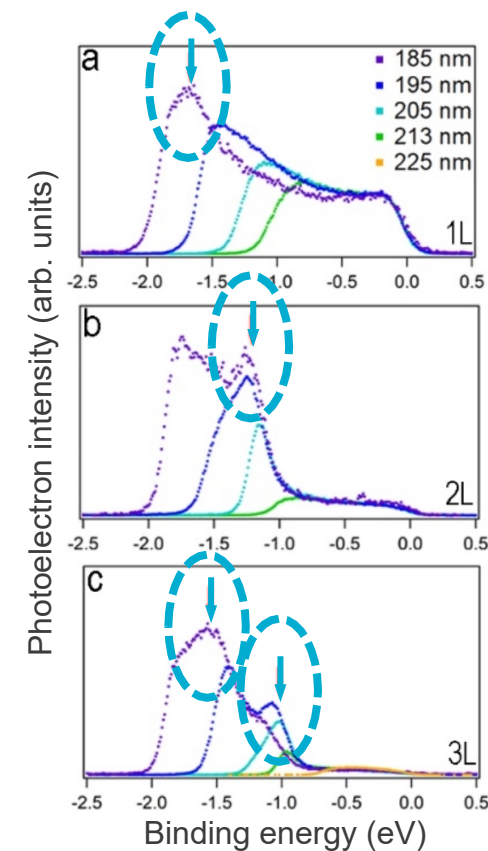
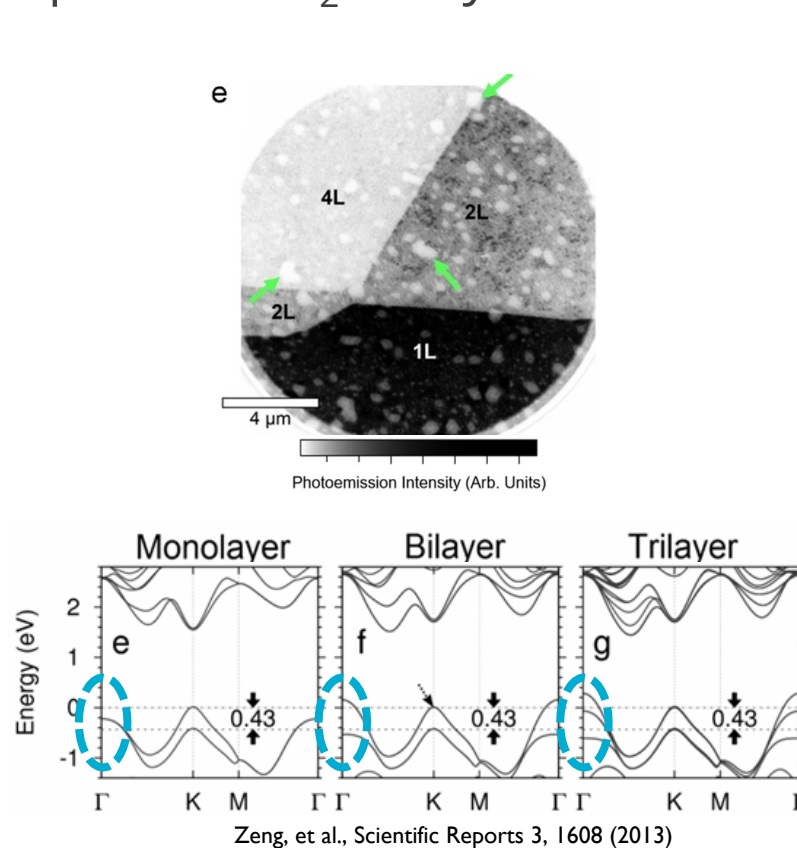
- System 2: Reflow & recrystallization create WS_2 -Au(111) interface with **pseudo-epitaxial** relation

- Photoelectron spectra show characteristic splitting of the highest occupied states at Γ -point in this pseudo-epitaxial WS_2 -Au system



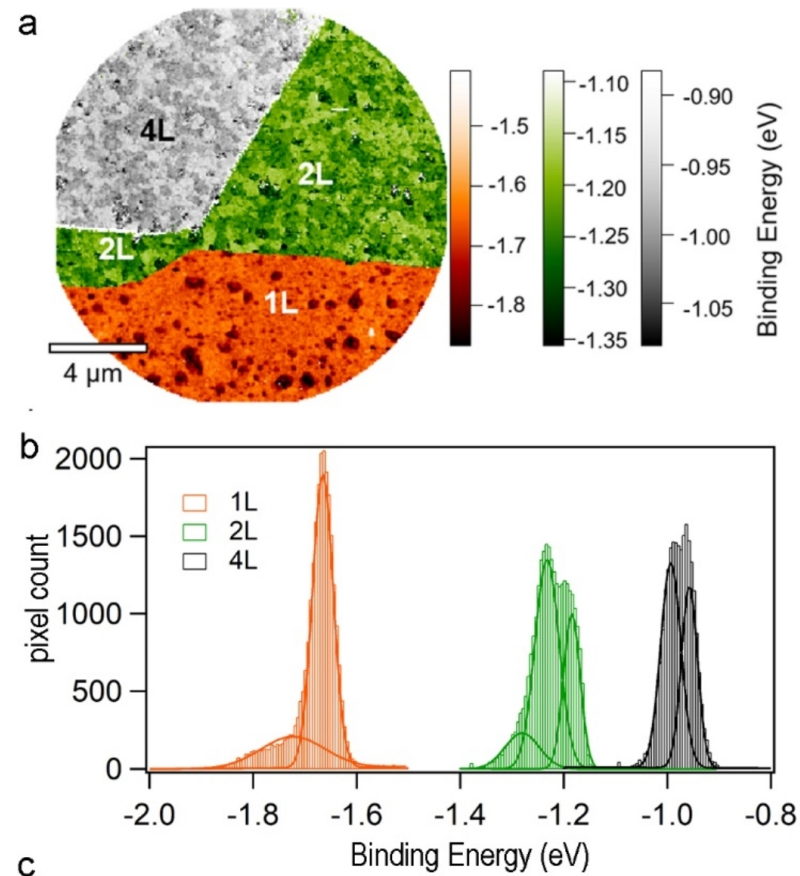
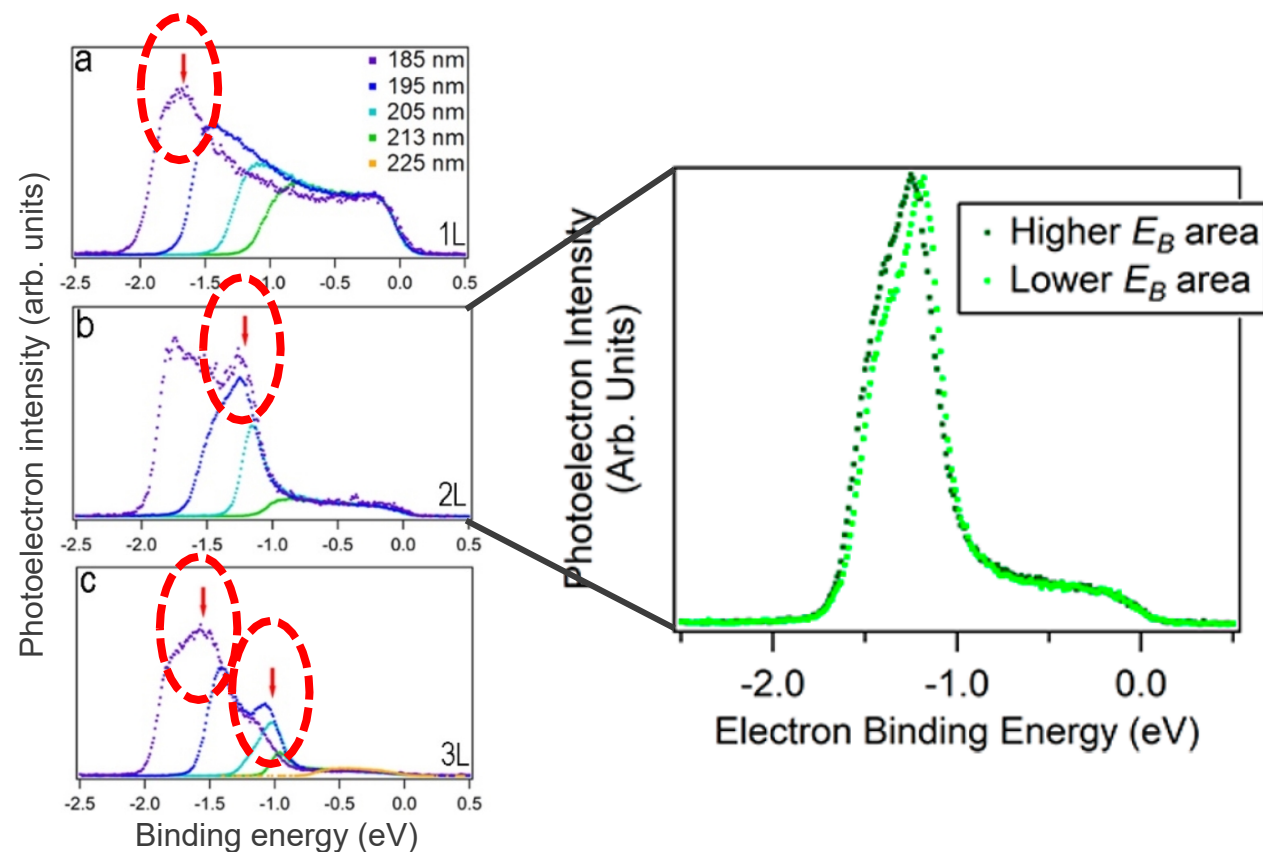
EBSD confirmed pseudo-epitaxial interface

Fonseca, et al., Nature Communications 11, 5 (2020)



Thomas, et al., ACS Nano, 15, 18060, 2021

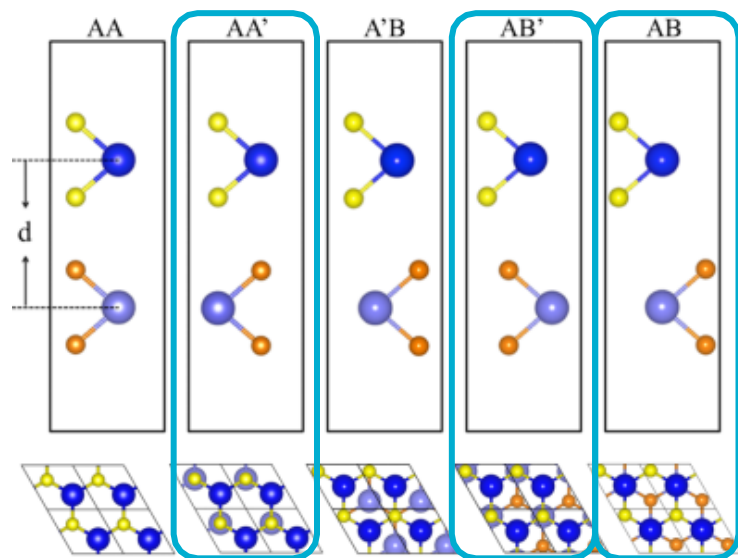
We found local variations of the Γ -point peak positions in multilayer WS_2



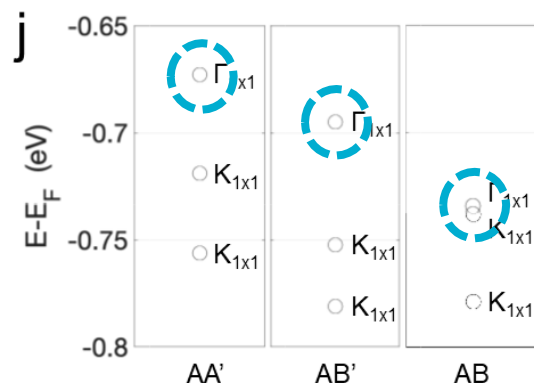
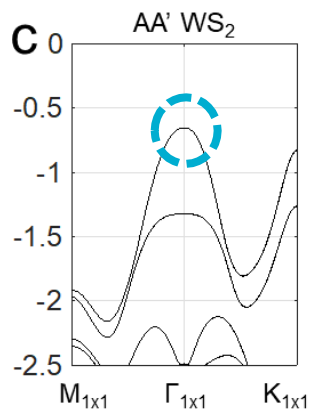
- The variations of the Γ -point peak position are 30-50meV
- Shape & size of the variations match the crystal grains in the Au-film
- The variations found in multilayer, but absent in single layer

Hypothesis: layer slippage due to the strong adhesion between WS_2 & Au?

DFT modeling supports the layer slippage model

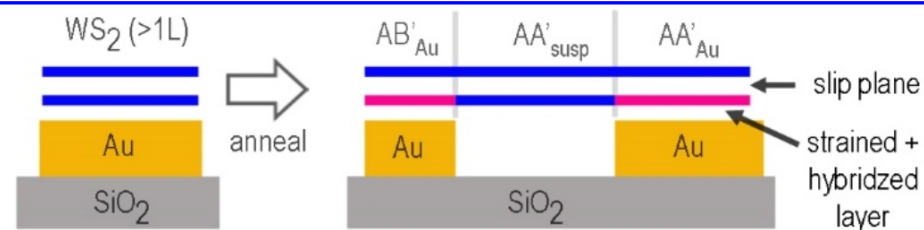


He, et al., PRB 89, 075409 (2014)



- Compared stacking sequences for 2L: AA', AB', and AB
 - AA' common for bulk WS₂
 - Alignment of one layer is slightly shifted with respect to another
- 20-50meV variations of Γ -point state depending on the stacking sequence
 - Similar to the PEEM result of 30-50meV variations
- Support the metal adhesion-induced layer slippage model resulting in the WS₂'s local electronic structure variations

Conclusion: electronic properties of TMD is **altered mechanically** by the metal

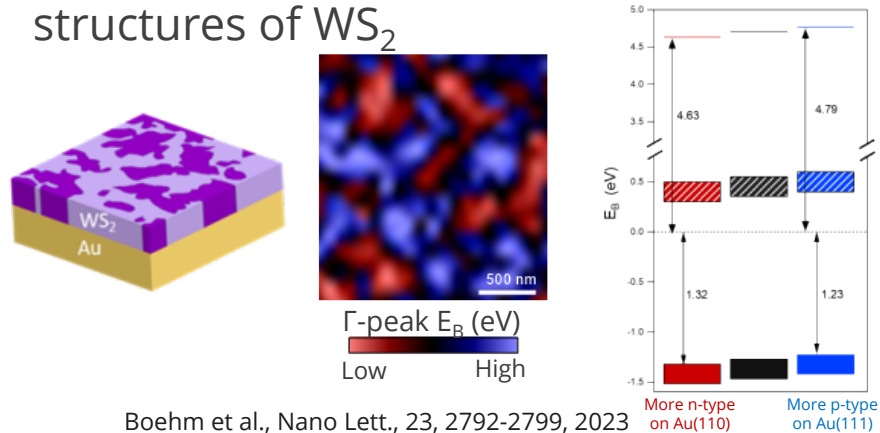


Take-home message:

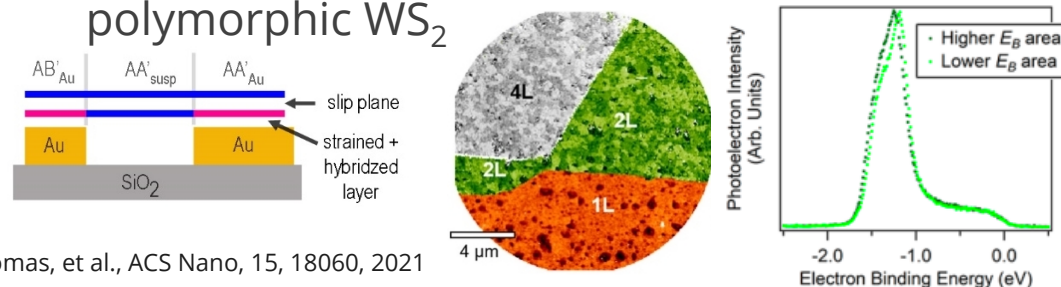
- Microstructures of Au films plays important role in the electronic properties of the WS₂-Au contacts

Concluding remarks

- Upside-down geometry allows direct access to semiconductor electronic properties & help us understand the metal contacts
- Microstructures of Au films plays important role at WS₂-Au contacts
 - Au grains' facet govern the local electronic structures of WS₂



- Layer slippage induces stacking variation & polymorphic WS₂



Special thanks:

- WS₂-Au interface interactions

N. Bartelt, C. Smyth, F. Leonard, C. J. Thomas, T.-M. Lu, R. G. Copeland, P. Mantos

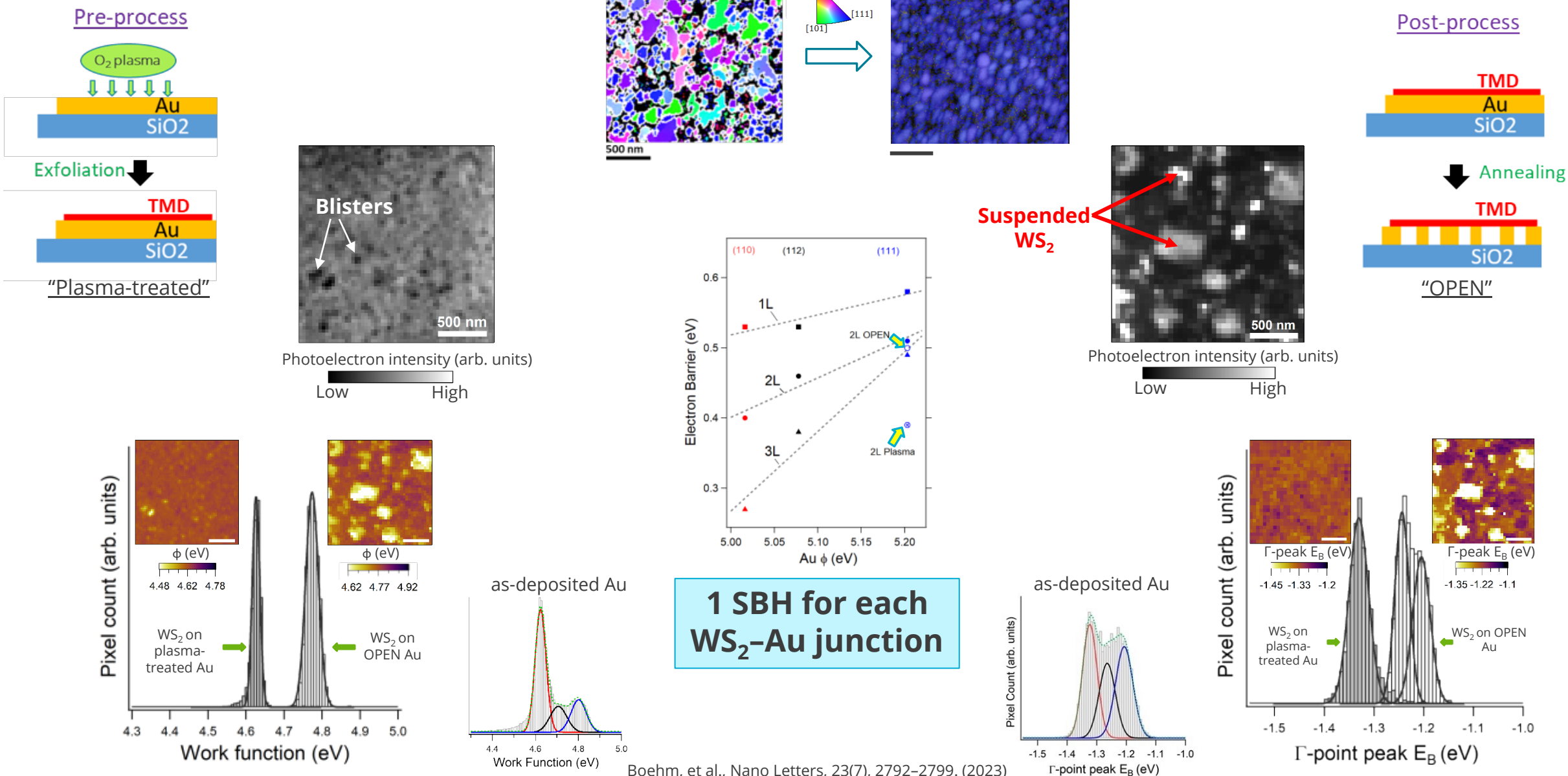
Announcement:

Looking for postdoc candidate: investigating the optical resonances in TMD disk structures

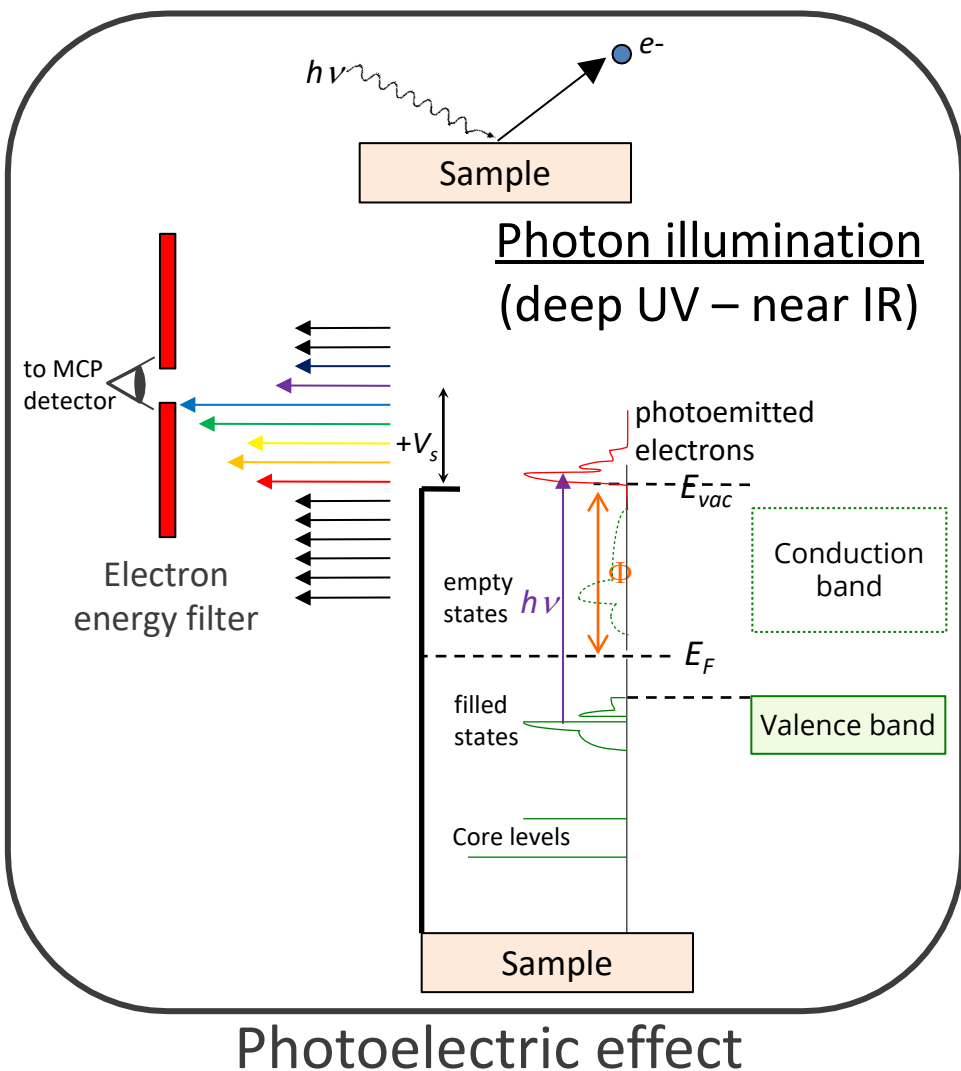
Thank you for your attention!



TMD on OPEN and Plasma-treated Au yield more uniform electronic structures



Reimagining what we can do with photoelectron imaging



Transition probability

Occupied electronic density of state

$$w_{i \rightarrow f} \propto \left| \langle f | H^{int} | i \rangle \right|^2 \delta(E_f - E_i - h\nu)$$

$$H^{int} = \frac{1}{2mc} (\mathbf{A} \cdot \mathbf{p}_{op} + \mathbf{p}_{op} \cdot \mathbf{A})$$

Final state

Initial state

Energy conservation

Hamiltonian for the interaction

Vector potential of the electromagnetic radiation

Momentum operator of the electron

Electromagnetic field

Photoelectron yield varies strongly due to electromagnetic field distribution & occupied electron density of states

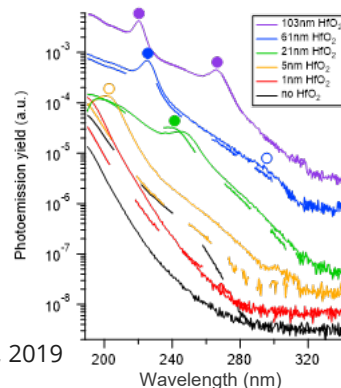
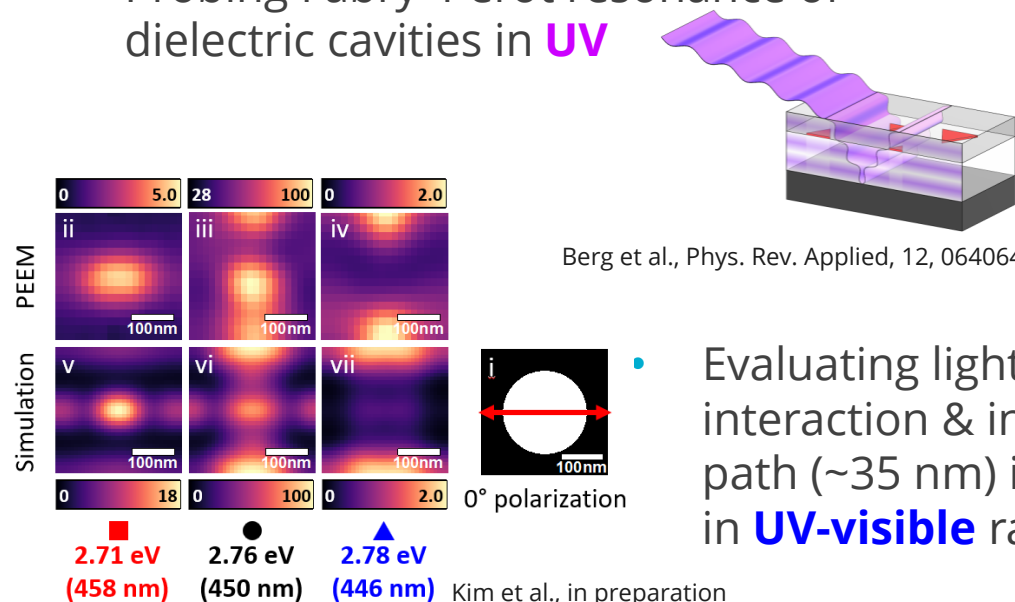
Light-matter interactions & electronic properties are probed based on the photoelectron intensity from the nanoscale materials

We examine electronic & optical properties using PEEM

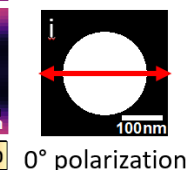


Electromagnetic field imaging

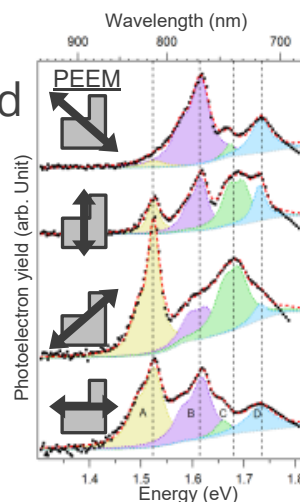
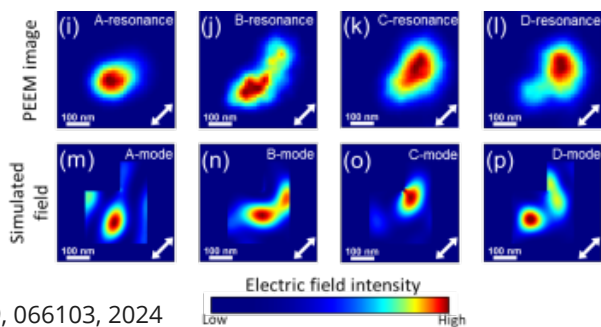
- Probing Fabry-Pérot resonance of dielectric cavities in **UV**



- Evaluating light-matter interaction & inelastic mean-free path (~ 35 nm) in Mie metasurface in **UV-visible** range

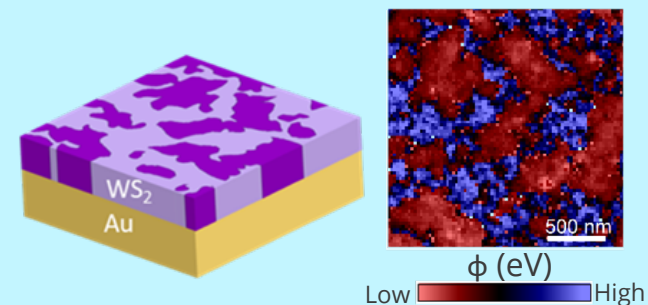


- Imaging **visible-near IR** resonances in Bound states in the continuum metasurfaces



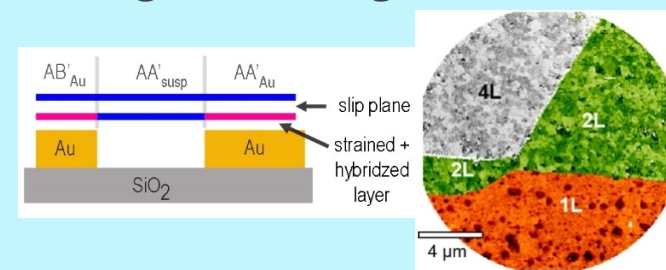
Electronic structures of interfaces between WS_2 & gold

- Crystal facets of Au grains govern the local electronic structures of WS_2



Boehm et al., Nano Lett., 23, 2792-2799, 2023

- Strong interaction induced layer slippage between WS_2 & Au grains resulting in stacking variation



Thomas, et al., ACS Nano, 15, 18060, 2021